

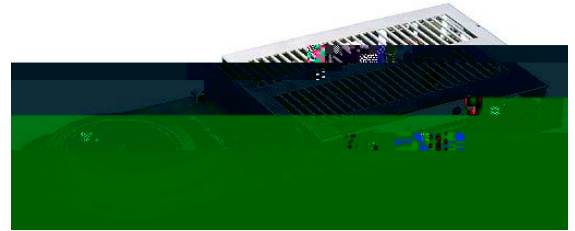
V_{DRM}	=	4500 V
I_{TGQM}	=	4000 A
I_{TSM}	=	32×10^3 A
$V_{(T0)}$	=	1.4 V
r_T	=	0.325 mW
$V_{DC-link}$	=	2800 V

Asymmetric Integrated Gate-Commutated Thyristor

5SHY 35L4510

Doc. No. 5SYA1232-02 June 07

- High snubberless turn-off rating
- Optimized for medium frequency (<1 kHz) and wide temperature range
- High reliability
- High electromagnetic immunity
- Simple control interface with status feedback
- AC or DC supply voltage
- Contact factory for series connection



Blocking

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Rep. peak off-state voltage	V_{DRM}	Gate Unit energized			4500	V
Permanent DC voltage for 100 FIT failure rate of GCT	$V_{DC-link}$	Ambient cosmic radiation at sea level in open air. Gate Unit energized			2800	V
Reverse voltage	V_{RRM}	IGCT in off-state			17	V
		IGCT in on-state			10	V

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Rep. peak off-state current	I_{DRM}	$V_D = V_{DRM}$, Gate Unit energized			50	mA

Mechanical data (see Fig. 11, 12)

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	F_m		36	40	44	kN

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Pole-piece diameter	D_p	± 0.1 mm		85		mm
Housing thickness	H		25.3		25.8	mm
Weight	m				2.9	kg
Surface creepage distance	D_s	Anode to Gate	33			mm
Air strike distance	D_a	Anode to Gate	10			mm
Length	l	± 1.0 mm		439		mm
Height	h	± 1.0 mm		40		mm
Width IGCT	w	± 1.0 mm		173		mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

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GCT Data

On-state (see Fig. 3, 4, 5, 6, 14, 15)

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. average on-state current	$I_{T(AV)M}$	Half sine wave, $T_C = 85\text{ °C}$, Double side cooled			1700	A
Max. RMS on-state current	$I_{T(RMS)}$				2670	A
Max. peak non-repetitive surge on-state current	I_{TSM}	$t_p = 10\text{ ms}$, $T_j = 125\text{ °C}$, sine wave after surge: $V_D = V_R = 0\text{ V}$			32×10^3	A
Limiting load integral	I^2t				5.12×10^6	A^2s
Max. peak non-repetitive surge on-state current	I_{TSM}	$t_p = 30\text{ ms}$, $T_j = 125\text{ °C}$, sine wave after surge: $V_D = V_R = 0\text{ V}$			21×10^3	A
Limiting load integral	I^2t				6.62×10^6	A^2s
Stray inductance between GCT and antiparallel diode	L_D	Only relevant for applications with antiparallel diode to the IGCT			300	nH
Critical rate of rise of on-state current	di_T/dt_{cr}	For higher di_T/dt and current lower than 100 A an external retrigger puls is required.			200	A/ μs

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	V_T	$I_T = 4000\text{ A}$, $T_j = 125\text{ °C}$		2.35	2.7	V
Threshold voltage	$V_{(T0)}$	$T_j = 125\text{ °C}$			1.4	V
Slope resistance	r_T	$I_T = 1000...4000\text{ A}$			0.325	m Ω

Turn-on switching (see Fig. 14, 15)

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Critical rate of rise of on-state current	di_T/dt_{cr}	$f = 0.500\text{ Hz}$, $T_j = 125\text{ °C}$, $V_D = 2800\text{ V}$, $I_{TM} \leq 4000\text{ A}$			1000	A/ μs

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Turn-on delay time	t_{don}	$V_D = 2800\text{ V}$, $T_j = 125\text{ °C}$ $I_T = 4000\text{ A}$, $di/dt = V_D / L_i$ $L_i = 5\text{ }\mu\text{H}$ $C_{CL} = 10\text{ }\mu\text{F}$, $L_{CL} = 0.3\text{ }\mu\text{H}$			3.5	μs
Turn-on delay time status feedback	$t_{don SF}$				7	μs
Rise time	t_r				1	μs
Turn-on energy per pulse	E_{on}				1.5	J

Turn-off switching (see Fig. 7, 8, 10, 14, 15)

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. controllable turn-off current	I_{TGQM}	$V_{DM} \leq V_{DRM}$, $T_j = 125\text{ °C}$, $V_D = 2800\text{ V}$, $R_S = 0.65\text{ }\Omega$, $C_{CL} = 10\text{ }\mu\text{F}$, $L_{CL} \leq 0.3\text{ }\mu\text{H}$			4000	A

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Turn-off delay time	t_{doff}	$V_D = 2800\text{ V}$, $T_j = 125\text{ °C}$ $V_{DM} \leq V_{DRM}$, $R_S = 0.65\text{ }\Omega$ $I_{TGQ} = 4000\text{ A}$, $L_i = 5\text{ }\mu\text{H}$ $C_{CL} = 10\text{ }\mu\text{F}$, $L_{CL} = 0.3\text{ }\mu\text{H}$			7	μs
Turn-off delay time status feedback	$t_{doff SF}$				7	μs
Turn-off energy per pulse	E_{off}				19.5	22

Gate Unit Data

Power supply (see Fig. 2, 9, 10, 12, 13)

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Gate Unit voltage (Connector X1)	$V_{GIN,RMS}$	AC square wave amplitude (15 kHz - 100kHz) or DC voltage. No galvanic isolation to power circuit.	28		40	V
Min. current needed to power up the Gate Unit	$I_{GIN Min}$	Rectified average current see application note 5SYA 2031	2.1			A

Gate Unit power consuzp Tc () Tj0 Tc (Re)30 Tc () 0 Tc (e a89) Tj0.06 Tc (c) Tj0 06 Tc (s) Tj0 Tc (u) Tj .04332 Tc (A) T

Thermal

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Junction operating temperature	T_{vj}		-40		125	°C
Storage temperature range	T_{stg}		-40		60	°C
Ambient operational temperature	T_a		-40		50	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction-to-case of GCT	$R_{th(j-c)}$	Double side cooled			8.5	K/kW
Thermal resistance case-to-heatsink of GCT	$R_{th(c-h)}$	Double side cooled			3	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i(1 - e^{-t/\tau_i})$$

i	1	2	3	4
R_i (K/kW)	5.562	1.527	0.868	0.545
τ_i (s)	0.5119	0.0896	0.0091	0.0024

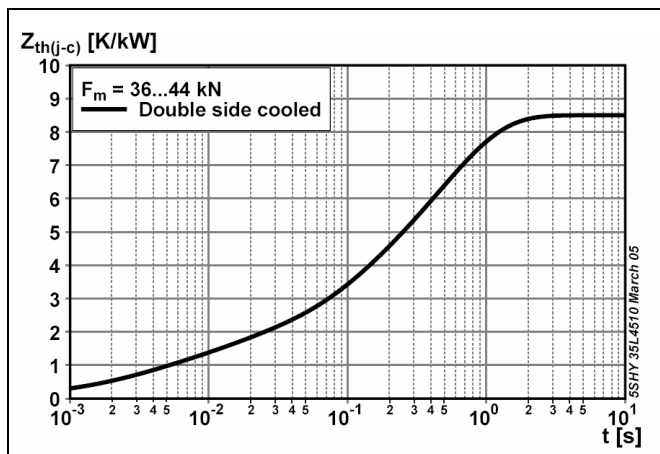


Fig. 1 Transient thermal impedance (junction-to-case) vs. time (max. values)

Max. Turn-off current for Lifetime operation

- calculated lifetime of on-board capacitors 20 years
- with slightly forced air cooling (air velocity > 0.5 m/s)
- strong air cooling allows for increased ambient temperature

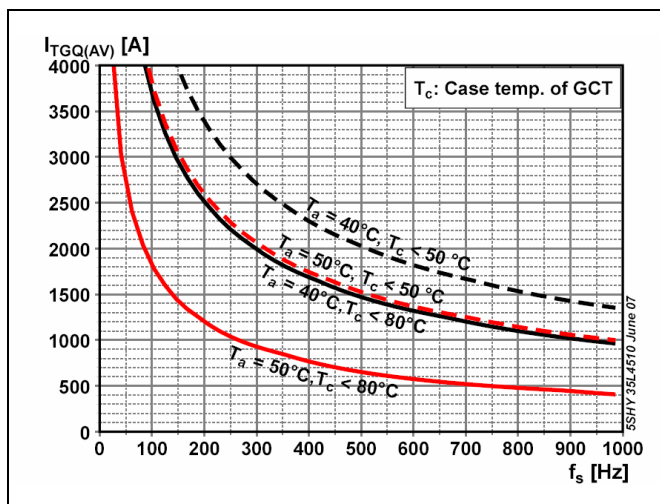


Fig. 2 Max. turn-off current vs. frequency for lifetime operation

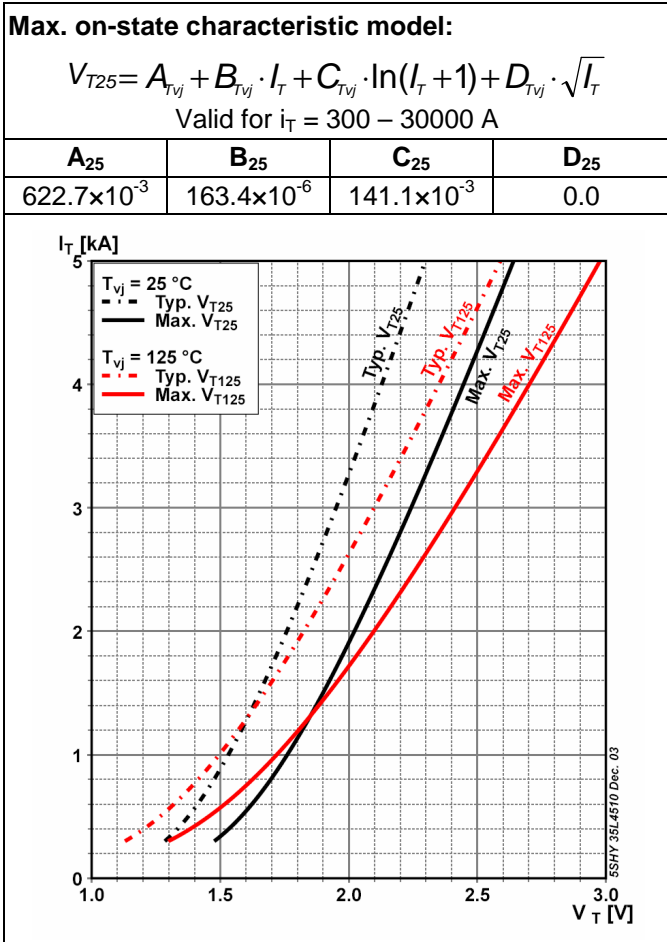


Fig. 3 GCT on-state voltage characteristics

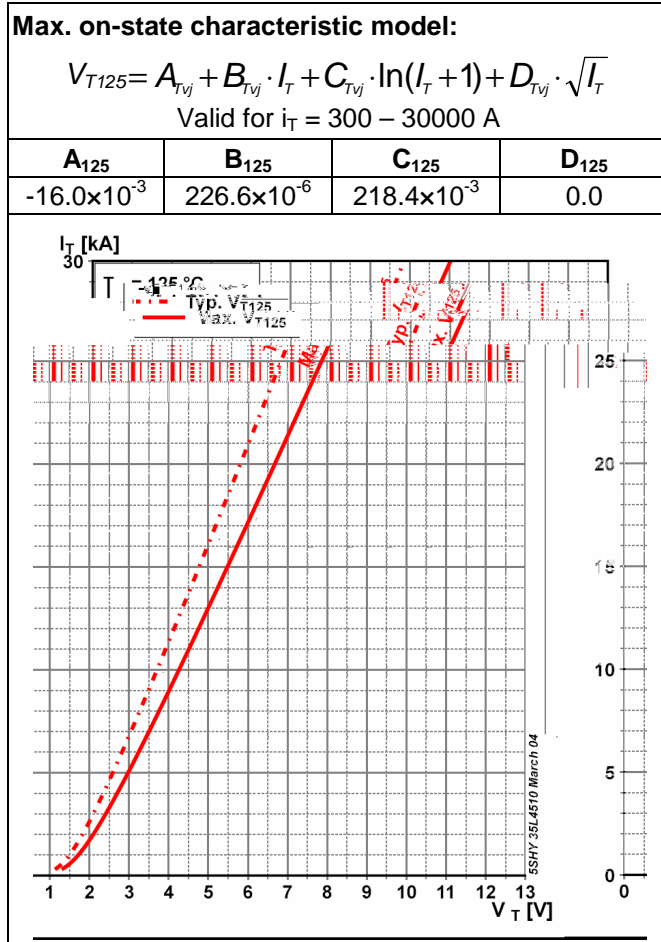


Fig. 4 GCT on-state voltage characteristics

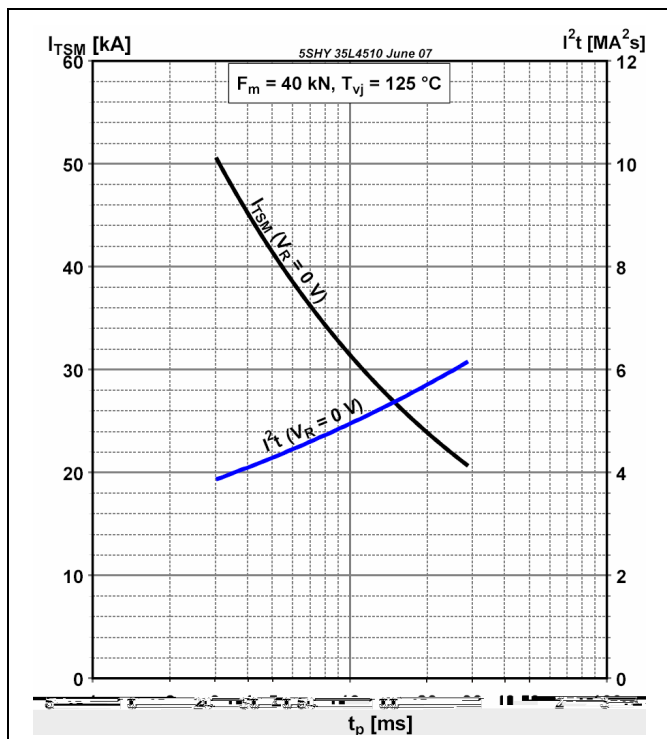


Fig. 5 Surge on-state current vs. pulse length, half-sine wave

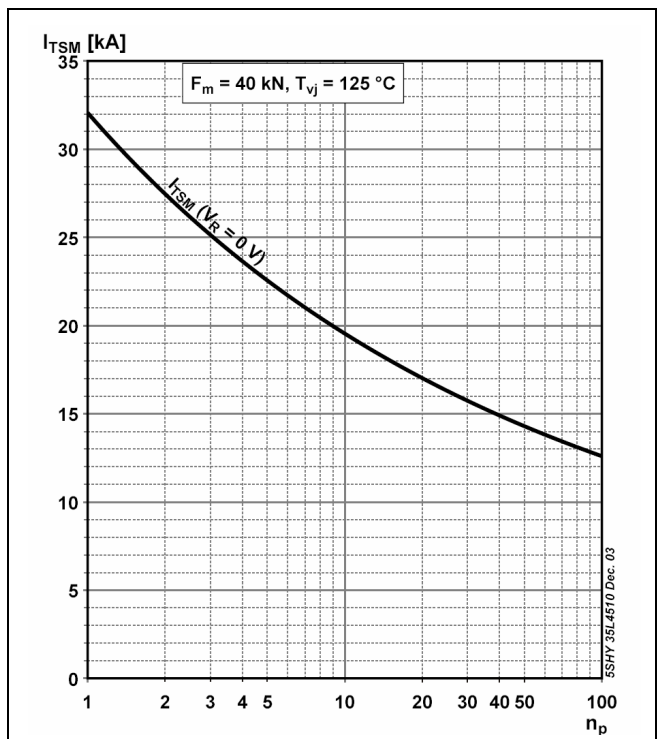


Fig. 6 Surge on-state current vs. number of pulses, half-sine wave, 10 ms, 50Hz

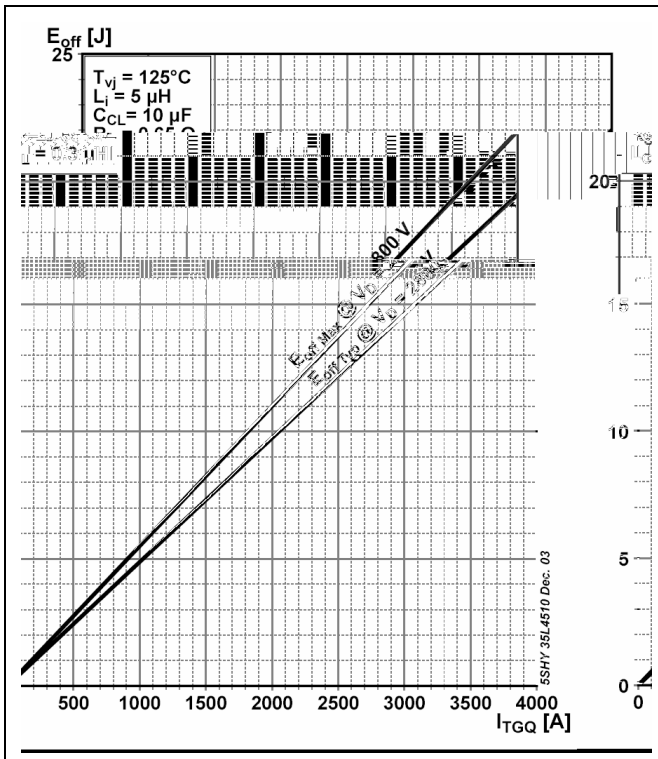


Fig. 7 GCT turn-off energy per pulse vs. turn-off current

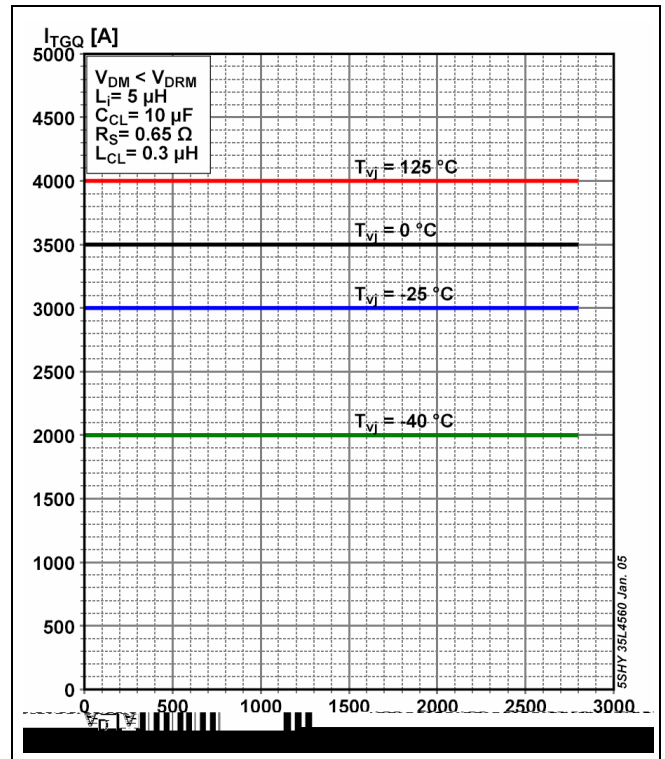


Fig. 8 Safe Operating Area

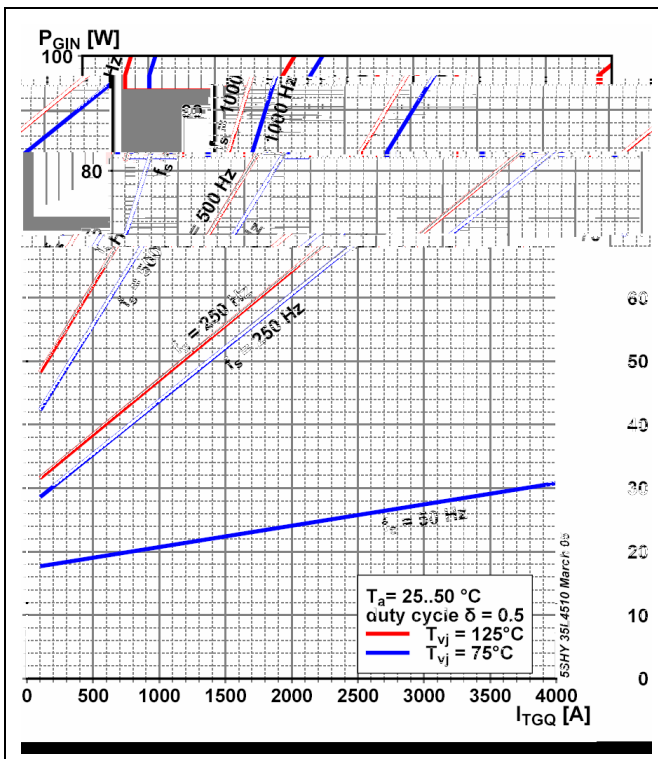


Fig. 9 Max. Gate Unit input power in chopper mode

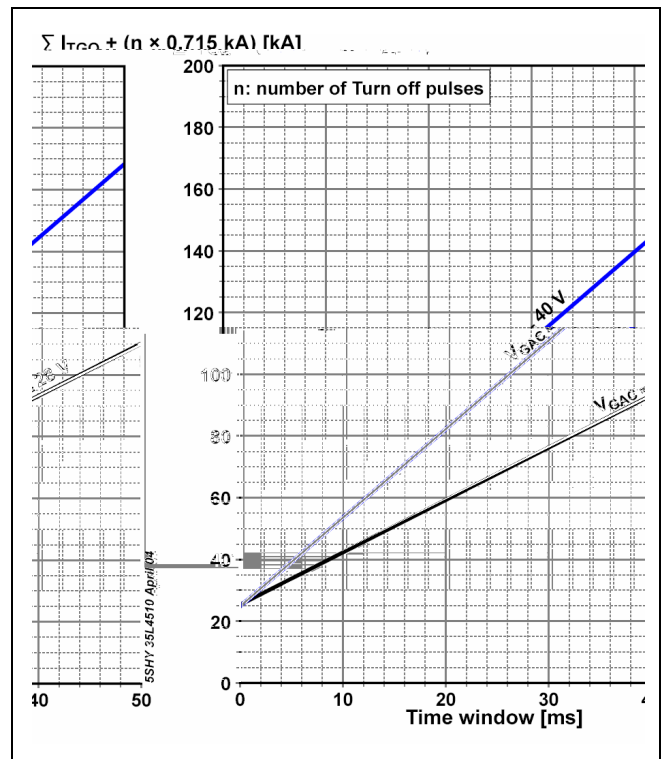


Fig. 10 Burst capability of Gate Unit



Related documents:

5SYA 2031	Applying IGCT Gate Units
5SYA 2032	Applying IGCTs
5SYA 2036	Recommendations regarding mechanical clamping of Press Pack High Power Semiconductors
5SYA 2046	Failure rates of IGCTs due to cosmic rays
5SYA 2048	Field measurements on High Power Press Pack Semiconductors
5SYA 2051	Voltage ratings of high power semiconductors
5SZK 9107	Specification of environmental class for pressure contact IGCTs, OPERATION available on request, please contact factory

Please refer to <http://www.abb.com/semiconductors> for current version of documents.

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